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Contents

ix	Authors
xiii	Conference Committee
	KEYNOTE SESSION
9426 02	Optical lithography with and without NGL for single-digit nanometer nodes
	(Keynote Paper) [9426-1]
	PUSHING OPTICAL LIMIT
9426 04	Evolving optical lithography without EUV (Invited Paper) [9426-3]
9426 05	Mask 3D induced phase and the mitigation by absorber optimization (Invited Paper)
	[9426-4]
9426 06	Patterning process exploration of metal 1 layer in 7nm node with 3D patterning flow
	simulations [9426-5]
	IMAGE AND PROCESS CONTROL
9426 07	Impact of bandwidth on contrast sensitive structures for low k1 lithography [9426-6]
0.407.00	
9426 08	Solution for high-order distortion on extreme illumination condition using computational prediction method [9426-7]
	prediction method [7420 7]
9426 09	Optimum ArFi light source bandwidth for 10nm node logic imaging performance [9426-8]
0.407.00	6:
9426 OB	Single lithography exposure edge placement model [9426-10]
	NON-IC APPLICATIONS
9426 OC	Multicolor, visible-light nanolithography (Invited Paper) [9426-11]
9426 OD	Progresses in 300mm DUV photolithography for the development of advanced silicon
, 120 02	photonic devices (Invited Paper) [9426-12]
.	
9426 OE	Double-sided diffractive photo-mask for sub-500nm resolution proximity i-line mask-aligner
	lithography [9426-13]
9426 OF	Optimization methods for 3D lithography process utilizing DMD-based maskless grayscale
	photolithography system [9426-14]

	MASK TOPOGRAPHY: JOINT SESSION WITH CONFERENCES 9422 AND 9426
9426 OH	Mask-induced best-focus-shifts in DUV and EUV lithography [9426-16]
9426 OI	Intensity and phase fields behind phase shifting masks studied with high resolution interference microscopy [9426-17]
	MULTIPLE PATTERNING AND SMO
9426 OJ	Study of cut mask lithography options for sub-20nm metal routing [9426-18]
9426 OK	Inverse lithography using sparse mask representations [9426-19]
9426 OL	RET selection on state-of-the-art NAND flash [9426-20]
9426 OM	Pixel-based ant colony algorithm for source mask optimization [9426-21]
9426 ON	Low-contrast photoresist development model for OPC applications at 10nm node [9426-22]
	MASK AND WAFER TOPOGRAPHY MODELING
9426 00	Characterizing the dependence of thick-mask edge effects on illumination angle using AIMS images (CYMER Best Student Paper Award in Microlithography) [9426-23]
9426 OP	Accurate, full chip 3D electromagnetic field model for non-Manhattan mask corners [9426-24]
9426 OQ	A pattern- and optics-independent compact model of Mask3D under off-axis illumination with significant efficiency and accuracy improvements [9426-25]
9426 OR	Printing circuits with 4nm feature size: similarities and differences between EUV and optical lithographies [9426-26]
9426 OS	Rigorous wafer topography simulation for investigating wafer alignment quality and robustness [9426-27]
	OPC AND MODELING
9426 OT	Investigating deprotection-induced shrinkage and retro-grade sidewalls in NTD resists [9426-29]
9426 OU	Alternative to ILT method for high-quality full-chip SRAF insertion [9426-30]
9426 OV	Uncertainty aware site selection method for OPC model calibration [9426-31]
9426 OW	Experiments using automated sample plan selection for OPC modeling [9426-32]

9426 OX	Optical proximity correction with hierarchical Bayes model [9426-33]
9426 OY	Application of SEM-based contours for OPC model weighting and sample plan reduction [9426-34]
_	DFM (DESIGN AND LITHO OPTIMIZATION): JOINT SESSION WITH CONFERENCES 9426 AND 9427
9426 10	Hot spots prediction after etching process based on defect rate [9426-36]
9426 11	Hybrid OPC flow with pattern search and replacement [9426-37]
	OVERLAY OPTIMIZATION: JOINT SESSION WITH CONFERENCES 9424 AND 9426
9426 12	Overlay improvement methods with diffraction based overlay and integrated metrology [9426-38]
9426 13	Intra-field overlay correction for illumination based distortion [9426-39]
9426 14	Wafer to wafer overlay control algorithm implementation based on statistics [9426-40]
	TOOLINGS
9426 16	Immersion and dry scanner extensions for sub-10nm production nodes [9426-46]
9426 17	Latest performance of ArF immersion scanner NSR-S630D for high-volume manufacturing
	for 7nm node [9426-42]
9426 18	for 7nm node [9426-42] New ArF immersion light source introduces technologies for high-volume 14nm manufacturing and beyond [9426-43]
9426 18 9426 19	New ArF immersion light source introduces technologies for high-volume 14nm
	New ArF immersion light source introduces technologies for high-volume 14nm manufacturing and beyond [9426-43] Total lithography system based on a new application software platform enabling smart
9426 19	New ArF immersion light source introduces technologies for high-volume 14nm manufacturing and beyond [9426-43] Total lithography system based on a new application software platform enabling smart scanner management [9426-44] Green solution: 120W ArF immersion light source supporting the next-generation
9426 19	New ArF immersion light source introduces technologies for high-volume 14nm manufacturing and beyond [9426-43] Total lithography system based on a new application software platform enabling smart scanner management [9426-44] Green solution: 120W ArF immersion light source supporting the next-generation multiple-pattering lithography [9426-45]
9426 19 9426 1A	New ArF immersion light source introduces technologies for high-volume 14nm manufacturing and beyond [9426-43] Total lithography system based on a new application software platform enabling smart scanner management [9426-44] Green solution: 120W ArF immersion light source supporting the next-generation multiple-pattering lithography [9426-45] POSTERS: IMAGE AND PROCESS CONTROL Comparing the experimental resist pattern width with aerial image intensity in high-NA

	POSTERS: MASK AND WAFER TOPOGRAPHY
9426 1F	Reducing the substrate dependent scanner leveling effect in low-k1 contact printing [9426-50]
9426 1G	A fast and flexible library-based thick-mask near-field calculation method [9426-51]
9426 1H	Focus shift impacted by mask 3D and comparison between Att. PSM and OMOG [9426-52]
	POSTERS: MULTIPLE PATTERNING AND SMO
9426 1J	120W ArF laser with high-wavelength stability and efficiency for the next-generation multiple-patterning immersion lithography [9426-54]
9426 1K	Forbidden pitches: causes, source optimization, and their role in design rules [9426-55]
9426 1L	Source optimization using particle swarm optimization algorithm in photolithography [9426-79]
_	POSTERS: NON-IC APPLICATIONS
9426 1M	Advanced Mask Aligner Lithography (AMALITH) [9426-56]
	POSTERS: OPC MODEL
9426 10	An improved virtual aberration model to simulate mask 3D and resist effects [9426-58]
9426 1P	Evaluation of compact models for negative-tone development layers at 20/14nm nodes [9426-59]
9426 1Q	Photoresist 3D profile related etch process simulation and its application to full chip etch compact modeling [9426-60]
9426 1R	Resist profile modeling with compact resist model [9426-61]
9426 18	Impacts of post OPC shapes on pattern [9426-62]
9426 1T	Calibrating etch model with SEM contours [9426-78]
	POSTERS: OPTICAL PROXIMITY CORRECTION
9426 1U	7nm logic optical lithography with OPC-Lite [9426-63]
9426 1V	OPC solution by implementing fast converging methodology [9426-64]

9426 1W	The comparison of various strategies of setting up an OPC repair flow with respect to process window constraints [9426-65]
9426 1X	Model-based Hot Spot Fixing (HSF) by using target point control function [9426-66]
9426 1Y	Sub-Resolution Assist Feature (SRAF) printing prediction using logistic regression [9426-67]
9426 1Z	Accurate and fast computation of transmission cross coefficients [9426-68]
9426 21	The study of lithography conditions to use advanced resist performance properly [9426-70]
	POSTERS: TOOLINGS
9426 23	Modeling and simulation of the beam steering unit [9426-72]
9426 24	DUV ArF light source automated gas optimization for enhanced repeatability and availability [9426-73]
9426 25	Performance of ETC controller in high-volume production [9426-74]
9426 26	Enabling CoO improvement thru green initiatives [9426-75]
9426 27	New robust and highly customizable light source management system [9426-76]
9426 28	Extending green technology innovations to enable greener fabs [9426-77]

Proc. of SPIE Vol. 9426 942601-8

Authors

Numbers in the index correspond to the last two digits of the six-digit citation identifier (CID) article numbering system used in Proceedings of SPIE. The first four digits reflect the volume number. Base 36 numbering is employed for the last two digits and indicates the order of articles within the volume. Numbers start with 00, 01, 02, 03, 04, 05, 06, 07, 08, 09, 0A, 0B...0Z, followed by 10-1Z, 20-2Z, etc.

Abdo, Amr, 0W Ackmann, Paul, 0T Adam, Kostas, OP Affentauschegg, Cedric, 08 Aggarwal, Tanuj, 18, 24 Algana, Paolo, 07, 09, 1D Allouti, Nacima, 0D An, Yongbae, 1X Aoyama, Hajime, 21 Apostol, Ştefan, OK, 1K, 1Z Axelrad, Valery, 1U Babcock, Carl P., 11 Bachmann, Michael, 06 Bailey, Todd, 0Y Barnola, Sébastien, OD Barouch, Eytan, OR Baselmans, Jan, 08, 09 Batarseh, Fadi, 11

Bérard-Bergery, Sébastien, 0D

Bibby, T., 18

Baudot, Charles, 0D

Bornebroek, Frank, 16 Botter, Herman, 16 Bourgin, Yannick, 0E Bramati, Arianna, 1M Brision, Stéphane, OD Brunner, Timothy, 13 Cacouris, T., 18 Casati, Nathalie, 0W Chang, C.S., 1F Chen, Ao, 1P Chen, K. C., 1F Chen, Quan, 21 Chen, Xuanbo, 1G Choi, Jaeseung, 1X Choi, Young-Sin, 08, 12 Chu, W. H., 1S Chunder, Anindarupa, 0J Chung, Angeline, 1P Ciofi, Ivan, 06

Clifford, Chris, 0P Comboroure, Corinne, 0D Conley, Will, 07, 18, 25 Connolly, Brid, 0O Coskun, Tamer H., 0V Croffie, Ebo, 0Q Dao, Hoang, 25 de Boeij, Wim P., 16 de Graaf, Roelof F., 16 Demmerle, Wolfgang, 06 Deng, Yunfei, 1P, 1R Do, Munhoe, 1X Dong, Lisong, 1G Dona, LiSona, 1H Droste, Richard, 16 Du, Yaojun, 1V, 1W Dunlap, David, 25 Enami, Tatsuo, 27, 28 Erdmann, Andreas, 0H Evanschitzky, Peter, 0H Feng, Jiayun, 23 Ferrotti, Thomas, 0D Finders, Jo, 05 Flagello, Donis G., 04 Flores, Ronnie, 25 Foong, Yee Mei, 1P, 1Y Fourkas, John T., OC Fryer, David, OP, 1P Fujii, Koichi, 10 Fukuda, Hitomi, 28 Funatsu, Takayuki, 17 Gabrani, Maria, 0W Galvier, Jean, 05 Gao, Jie, 1G Gao, Weimin, 06 Gavrilin, Dmitrii, OS Gays, Fabien, 0D Geh, Bernd, 08 Ghaida, Rani S., 11 Gillespie, Walter, 26 Gillijns, Werner, 06 Granik, Yuri, 1P, 1R Gräupner, Paul, 0H Graur, Ioana, 0Y Greiner, Andreas, 0S Gross, Eric, 18, 26

de Kort, Toine, 16

Halle, Scott, OY Haran, Don, 26 Hayakawa, Akira, 17 He, Xin, 23 He, Yuan, OL Herzig, Hans Peter, Ol Hikida, Yujiro, 17 Hirai, Yoshikazu, OF Hirayama, Toru, 17

Guo, Moran, 1H

Ha, Hun Hwan, 08, 12

Hitomi, Keiichiro, OY Ma, Xu, 1G Madhavan, Sriram, 11 Hofmann, Detlef, OS Mailfert, Julien, 09 Hou, Yachina, 07 Hsieh, Simon, 07 Mariolle, Denis, 0D Martinez, Pedro, 07 Huang, C. H., 1F Huang, S. Y., 1S Masaki, Kazuo, 19 Hurley, Paul, OK, 1K, 1Z Mason, Eric, 26 Hwang, Hyun Woo, 14 Matagne, Philippe, 06 Imai, Motokatsu, 10 Matsunaga, Takashi, 1A, 1J Ionescu, Radu-Cristian, OK, 1Z Matsunawa, Tetsuaki, OX Ishida, Keisuke, 1A, 1J Matsuyama, Tomoyuki, 19, 10, 21 Ishii, Hiroyuki, 1U McGowan, Sarah, 11 Ishiyama, Satoshi, 17 McLaren, Matthew G., 16 Jaiswal, Om, 0W Medvedev, Dmitry, 1P Janda, Eric, 08 Mehta, Sohan, OT Jantzen, Kenneth, 1T Melchior, J., 18 Jina, Nan, 13 Menezo, Sylvie, 0D Kakizaki, Kouji, 1A, 1J Mikami, Koji, 1U Kamohara, Itaru, OS Miller, Marshal, 0Y Kanaya, Reiji, 10 Minegishi, Yuji, 27, 28 Kang, Young-Seog, 08, 12, 14 Miyazawa, Tami, 21 Käsebier, Thomas, 0E Mizoguchi, Hakaru, 1A, 1J Kato, Yoshiki, OF Moeller, Holger, OS Kim, Sunny Jang-Sun, 08, 12 Morgana, Nicoló, OS Kim, Ryoung-Han, 0J Morgenfeld, Bradley, 13 Kim, Seongjin, 1X Nakashima, Toshiharu, 1C Kim, Young Ha, 08 Nakayama, Ryo, 1U Kim, Young Hoon, 12 Nam, Young-Sun, 08, 12 Kimura, Taiki, 10 Neumann, Jens Timo, 0H Kley, Ernst-Bernhard, 0E Neureuther, Andy, 0O Klostermann, Ulrich, OS Oberschmidt, James, 0W Koh, Kar Kit, 1Y O'Brien, Kevin, 24, 25 Kong, Jeong Heung, 12, 14 Ochiai, Hideyuki, 27 Kono, Hirotaka, 17, 19 Ohta, Takeshi, 1A, 1J, 27 Kopp, Christophe, 0D Oliver, Mike, 0P Kotani, Toshiva, 10 Omran, A., 1T Kumazaki, Takahito, 1A, 1J Oulmane, Mohamed, 06 Kuo, C. C., 1S Oyama, Kenichi, 1U Kuo, Hung-Fei, 0M Padmabandu, G. G., 26 Kurosu, Akihiko, 1A, 1J Pan, David Z., 0X Kwon, Oh-Sung, 08 Park, Seemoon, 19 Kye, Jongwook, 0J, 0T Pathak, Piyush, 11 Lafferty, Neal, 0L Pei, Jinhua, OL Lake, Matt, 25, 26 Pike, Michael, 13 Lam, Michael, OP Ping, Yang Y., 11 Lange, Falk, 00 Pistor, Thomas V., 0T Lee, Byeong Soo, 14 Ponomarenko, Mariya, 08 Li, Frederick, 0M Preuninger, Juergen, 0S Li, Sikun, 1E, 1L Puthankovilakam, Krishnaparvathy, Ol Li, Xiaopina, 23 Rechtsteiner, Greg, 09, 1D Li, Yanqiu, 1G Renwick, Stephen P., 04 Lin, Burn J., 02 Rizvi, Umar, 08 Saad, Yves, 06 Lin, H. T., 1S Lin, Qun Ying 10 Scharf, Toralf, 01 Liu, QingWei, 0L Schmoeller, Thomas, 06 Liu, Yansong, 1H Sczyrba, Martin, 00 Luan, Lan, 1Q Sei, Toshihiko, 21 Lucas, Kevin, 06 Shanker, Aamod, 00

Lutich, Andrey, 0U

Ma, Xiaoxu, OF

Shao, Chun, 21

Shao, Feng, OL

Shen, Lina, 1E Shi, Xuelong, OL Shibazaki, Yuichi, 17, 19 Shibuya, Masato, 1C Shin, Ju Hee, 08, 12 Shin, Si Woo, 12 Shirata, Yosuke, 17 Siefke, Thomas, 0E Simic, Aleks, 25 Slotboom, Daan, 08 Smayling, Michael C., 1U Somani, Shikha, 11 Song, Hua, ON, 1Q Song, Myeong Gyu, 14 Song, Zhiyang, 1H Souhaité, Aurélie, 0D Su, Xiaoiina, 1H Su, Yajuan, 1H Sugihara, Taro, 19 Szelag, Bertrand, OD Tabata, Osamu, OF Takada, Akira, 1C Takahisa, Kenji, 27, 28 Takemasa, Kengo, 21 Tan, Chin Boon, 1Y Tejnil, Edita, OP Thornes, Joshua, 18, 25 Timoshkov, Vadim, 09 Tomova, Zuleykhan, OC Tsai, Y. T., 1S Tseng, C. F., 1F Tsuchiya, Toshiyuki, OF Tsujita, Koichiro, 1U Tsushima, Hiroaki, 1A, 1J Tsuzuki, Takao, 10 Tyminski, Jacek K., OB Uehara, Yusaku, 17 Ujazdowski, Richard, 26 van Ballegoij, Rob, 16 van der Heijden, Rob W., 08 van der Sanden, Stefan, 08 van Kempen, Floris, OF van Keulen, Fred, OF Verma, Piyush, 11 Viswanathan, Ramya, OW Vizioz, Christian, 0D Voelkel, Reinhard, Ol, 1M Vogler, Uwe, 01, 1M Wakamoto, Shinji, 19 Waller, Laura, 00 Wang, Chenchen, 0J, 0T Wang, Jinchun, 23 Wang, Jingyu, 11 Wang, Lei, 1L Wang, Wuping, 21 Wang, Xiangzhao, 1E, 1L Wang, Yan, OJ, OT Watanabe, Yuki, 10 Watts, Josef, OW

Wehrung, Brian, 25

Wei, David, 0N, 0Q Wei, Yavi, 1H Weichelt, Tina, 01 Weichselbaum, Stefan, 16 Weisbuch, François, 1T Wiltshire, Timothy, 13 Wong, Patrick, 09 Woo, Youngtag, 0J Wu, Cheng-En, 0N, 1Q Wu, Wei-Chen, 0M Wu, Yixu, OT Wyman, John, 25 Yaegashi, Hidetami, 1U Yamauchi, Shohei, 1U Yan, Guanyong, 1E, 1L Yan, Qiliang, 0Q Yang, Chaoxing, 1L Yang, Elvis, 1F Yang, Hyunjo, 1X Yang, Qing, 1V, 1W Yang, T. H., 1F Yang, Wayne, 1Q Yang, Zhengkai, 21 Yeung, Michael S., OR Yim, Donggyu, 1X Yoo, Youngsun, 28 Yu, Bei, 0X Yuan, Lei, OJ, OT Yun, Sang Ho, 12 Zeitner, Uwe D., 0E, 0I Zeng, Jia, 0J Zhana, Charlie, 0N Zhang, Dong Qing, 1P, 1Y Zhang, Hongbo, 0Q Zhang, Hongxin, 1P Zuniaa, Christian, 1R Zurita, Omar, 09, 1D

Proc. of SPIE Vol. 9426 942601-12

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1 Keynote Session

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5 Mask Topography: Joint Session with Conferences 9422 and 9426 Ted Liang, Intel Corporation (United States) Hsu-Ting Huang, Taiwan Semiconductor Manufacturing Company Ltd. (Taiwan))

6 Multiple Patterning and SMO

Xuelong Shi, Semiconductor Manufacturing International Corporation (China)

Emily Gallagher, IMEC (Belgium)

7 Mask and Wafer Topography Modeling

John S. Petersen, Periodic Structures, Inc. (United States) **Young Seog Kang**, SAMSUNG Electronics Company, Ltd. (Korea, Republic of)

8 OPC and Modeling

Yuri Granik, Mentor Graphics Corporation (United States)

Peter D. Brooker, Synopsys, Inc. (United States)

9 DFM (Design and Litho Optimization): Joint Session with Conferences 9426 and 9427

Jongwook Kye, GLOBALFOUNDRIES Inc. (United States) **Andrew R. Neureuther**, University of California, Berkeley (United States)

Overlay Optimization: Joint Session with Conferences 9424 and 9426
 John C. Robinson, KLA-Tencor Corporation (United States)
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DSA Design for Manufacturability: Joint Session with Conferences 9423, 9426, and 9427

Michael A. Guillorn, IBM Thomas J. Watson Research Center (United States)

Sachiko Kobayashi, Toshiba Corporation (Japan)

Vivek K. Singh, Intel Corporation (United States)

12 Toolings

Soichi Owa, Nikon Corporation (Japan)

Daniel Sarlette, Infineon Technologies Dresden (Germany)

Proc. of SPIE Vol. 9426 942601-16